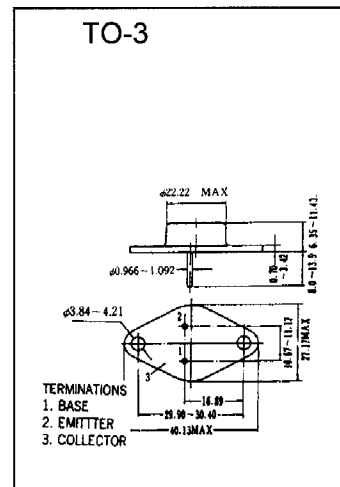


**BUW13A**

**NPN SILICON TRANSISTOR**

**SWITCHING REGULATORS PWM INVERTERS  
SOLENOID AND RELAY DRIVERS**

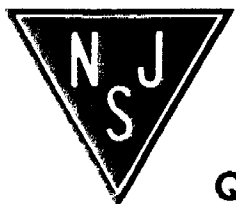


**ABSOLUTE MAXIMUM RATINGS (Ta=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	1000	V
Collector-Emitter Voltage	VCEO	450	V
Collector Current (DC)	IC	8	A
Collector Dissipation (Tc=25°C)	PC	175	W
Junction Temperature	Tj	200	°C
Storage Temperature	Tstg	-50~150	°C

**ELECTRICAL CHARACTERISTICS (Ta=25°C)**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	ICBO	VCB= 1000V , IE=0			10	µA
Collector Cutoff Current	ICEO	VCB=450V , IB=0			10	µA
DC Current Gain	hFE	VCE=5V , IC=10A	5			
Collector- Emitter Saturation Voltage	VCE(sat)	IC=6A , IB=0.6A			2.5	V



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

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